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IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

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In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors

founded by NXP

TYN16X-600CT

SCR

24 October 2016 — Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT186A (TO-220F) "full pack" plastic package intended for use in applications requiring high thermal cycling performance and high junction temperature capability ($T_{j(max)}$ = 150 °C).

2. Features and benefits

- High junction operating temperature capability
- High thermal cycling performance
- High voltage capability
- Planar passivated for voltage ruggedness and reliability

3. Applications

- Ignition circuits
- Motor control
- Protection circuits e.g. SMPS inrush current
- Voltage regulation

4. Quick reference data

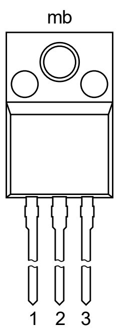
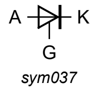
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	-	600	V
V_{RRM}	repetitive peak reverse voltage			-	-	600	V
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5		-	-	180	A
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms		-	-	198	A
T_j	junction temperature			-	-	150	°C
$I_{T(AV)}$	average on-state current	half sine wave; $T_h \leq$ 81 °C; Fig. 1		-	-	10.2	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_h \leq$ 81 °C; Fig. 2; Fig. 3		-	-	16	A
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 7		-	-	15	mA
Dynamic characteristics							

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		500	-	-	V/μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 TO-220F (SOT186A)	
2	A	anode		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

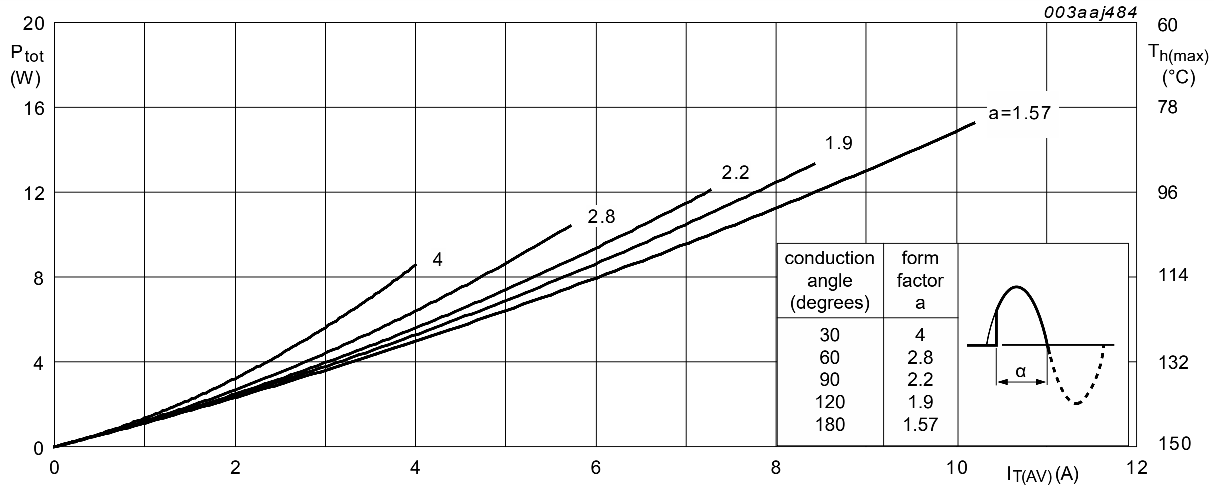
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
TYN16X-600CT	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

7. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	600	V
V_{RRM}	repetitive peak reverse voltage			-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_h \leq$ 81 °C; Fig. 1		-	10.2	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_h \leq$ 81 °C; Fig. 2; Fig. 3		-	16	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5		-	180	A
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms		-	198	A
I^2t	I^2t for fusing	t_p = 10 ms; SIN		-	162	A²s
dI_T/dt	rate of rise of on-state current	I_T = 40 A; I_G = 200 mA; dI_G/dt = 200 mA/µs		-	50	A/µs
I_{GM}	peak gate current			-	4	A
V_{RGM}	peak reverse gate voltage			-	5	V
P_{GM}	peak gate power			-	10	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	1	W
T_{stg}	storage temperature			-40	150	°C
T_j	junction temperature			-	150	°C



a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 1. Total power dissipation as a function of average on-state current; maximum values

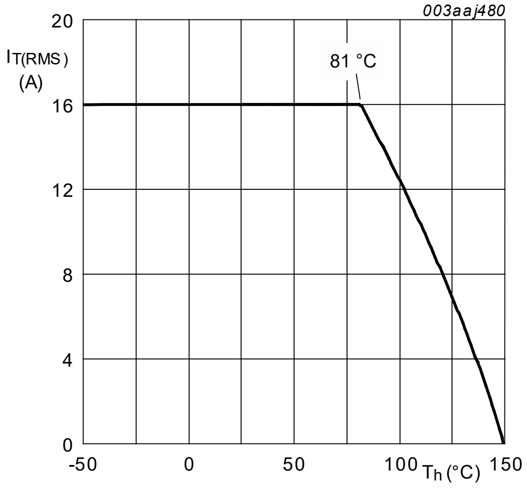
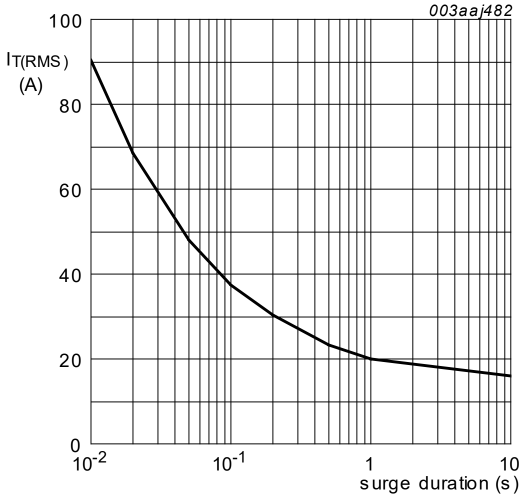
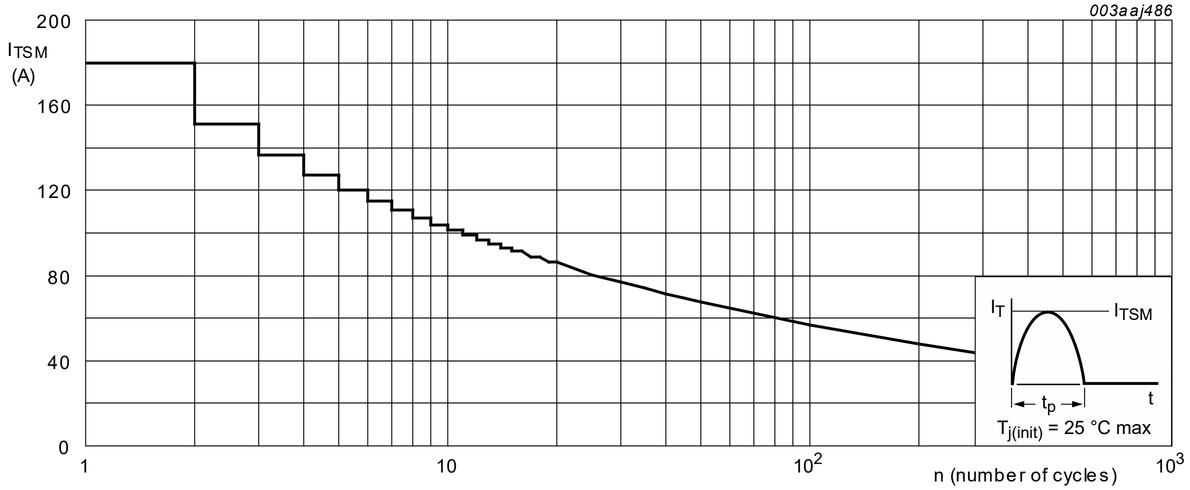


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values



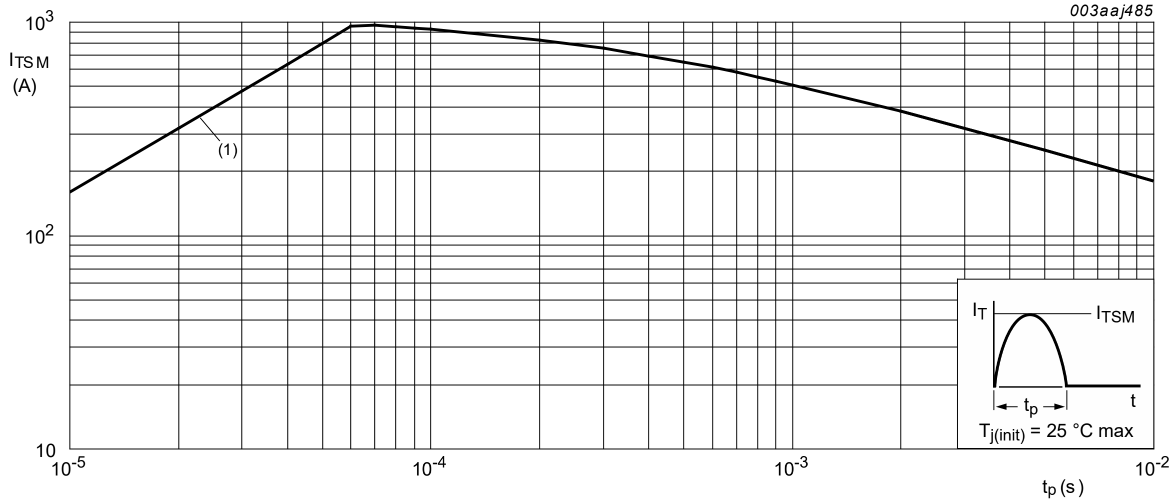
f = 50 Hz; T_h = 81 °C

Fig. 3. RMS on-state current as a function of surge duration; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



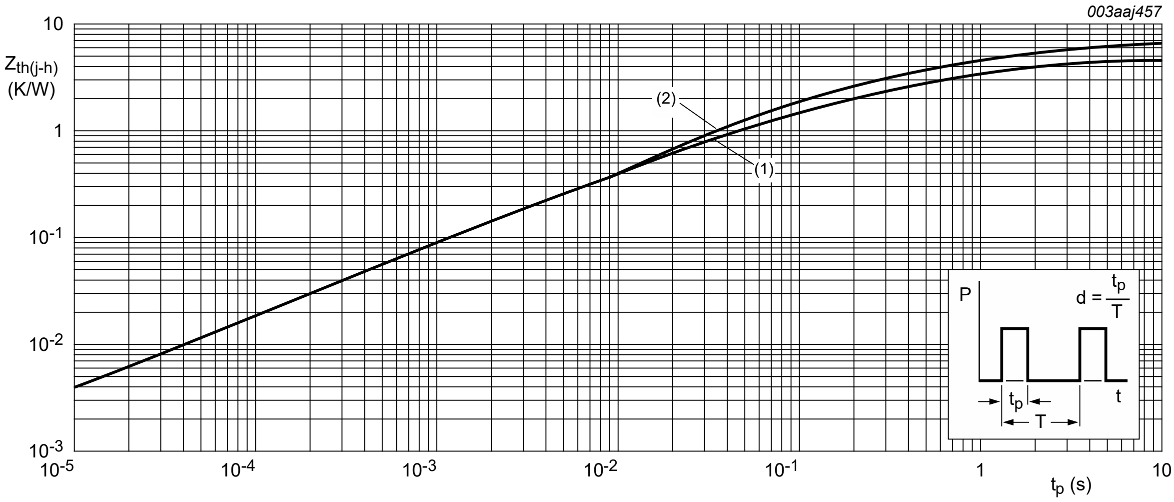
t_p ≤ 10 ms; (1) dI_T / dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig. 6		-	-	4.5	K/W
		without heatsink compound; Fig. 6		-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	55	-	K/W



(1) with heatsink compound
(2) without heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse width

9. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; T_h = 25 °C		-	-	2500	V
C_{isol}	isolation capacitance	from anode to external heatsink; f = 1 MHz; T_h = 25 °C		-	10	-	pF

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 7		-	-	15	mA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; T_j = 25 °C; Fig. 8		-	-	60	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	40	mA
V_T	on-state voltage	I_T = 32 A; T_j = 25 °C; Fig. 10		-	1.2	1.6	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 11		-	0.7	1.3	V
		V_D = 400 V; I_T = 0.1 A; T_j = 150 °C; Fig. 11		0.2	0.4	-	V
I_D	off-state current	V_D = 600 V; T_j = 150 °C		-	0.2	1	mA
I_R	reverse current	V_R = 600 V; T_j = 150 °C		-	0.2	1	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		500	-	-	V/μs
t_{gt}	gate-controlled turn-on time	I_{TM} = 40 A; V_D = 600 V; I_G = 100 mA; dI_G/dt = 5 A/μs; T_j = 25 °C		-	2	-	μs
t_q	commutated turn-off time	V_{DM} = 402 V; T_j = 125 °C; I_{TM} = 20 A; V_R = 25 V; $(dI_T/dt)_M$ = 30 A/μs; dV_D/dt = 50 V/μs; $R_{GK(ext)}$ = 100 Ω; (V_{DM} = 67% of V_{DRM})		-	70	-	μs

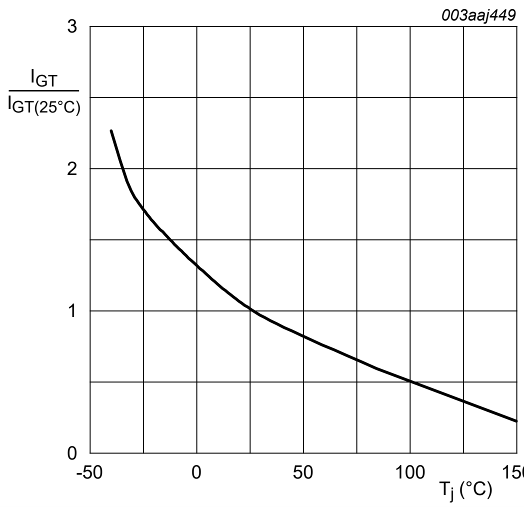


Fig. 7. Normalized gate trigger current as a function of junction temperature

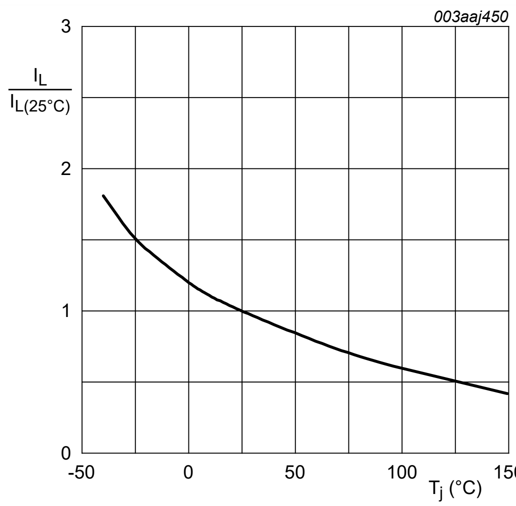


Fig. 8. Normalized latching current as a function of junction temperature

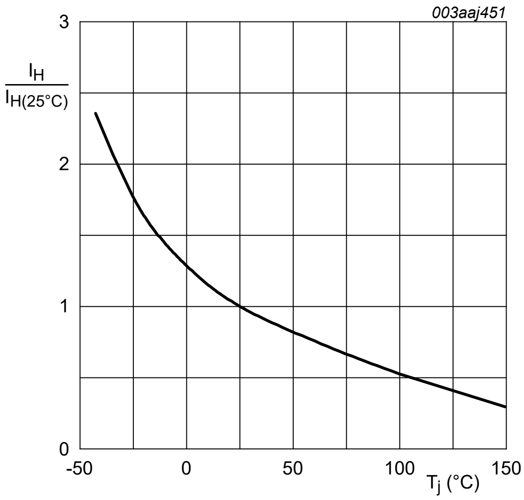
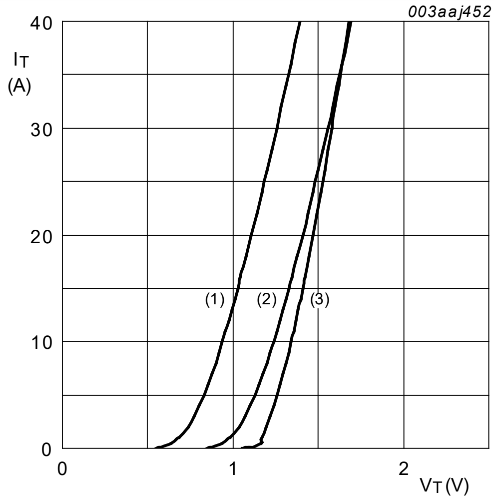


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 1.08 V; R_s = 0.0165 Ω
(1) T_j = 150 °C; typical values
(2) T_j = 150 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

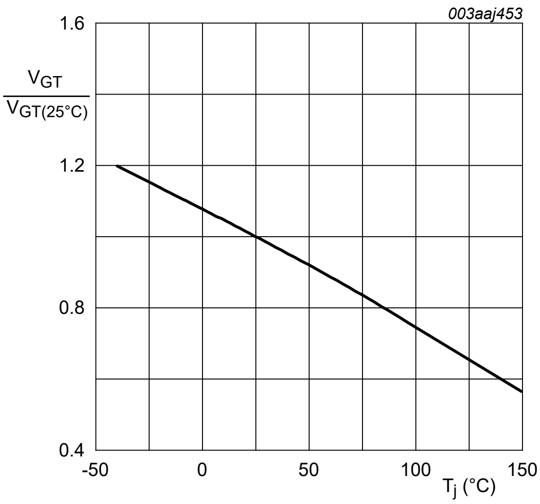
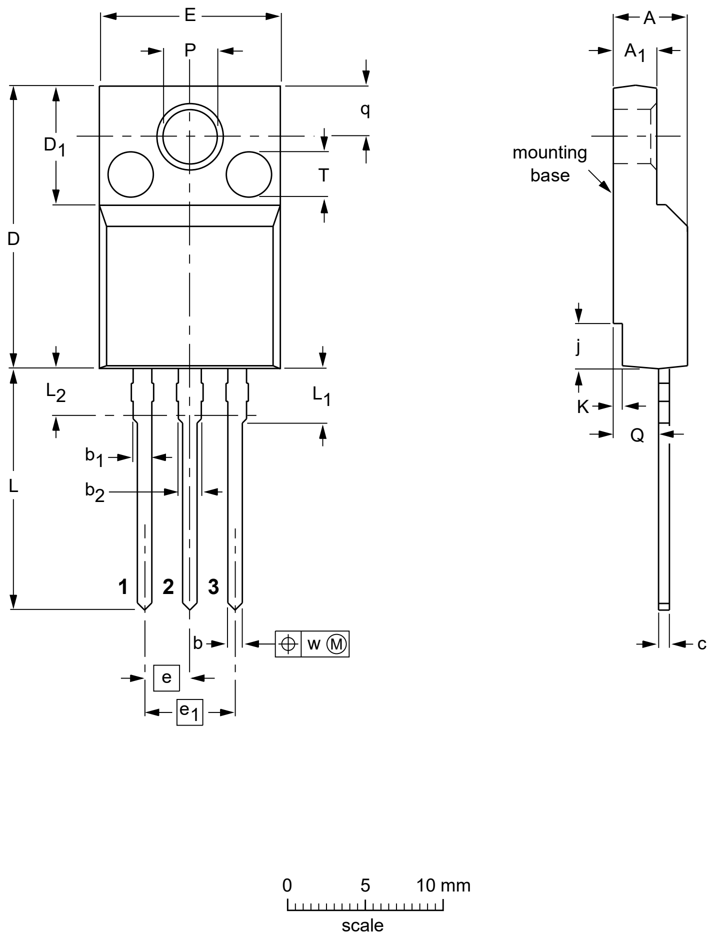


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	b_2	c	D	D_1	E	e	e_1	j	K	L	L_1	L_2 (1) max.	P	Q	q	T (2)	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

Notes

1. Terminal dimensions within this zone are uncontrolled.
2. Both recesses are # 2.5 × 0.8 max. depth

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT186A		3-lead TO-220F				~~02-04-09~~ 06-02-14

Fig. 12. Package outline TO-220F (SOT186A)

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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13. Contents

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Date of release: 24 October 2016